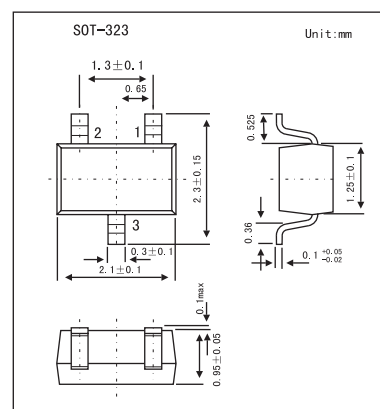


Silicon Schottky Barrier Diode

HSB88WA

■ Features

- Low reverse current, Low capacitance.
- CMLPAK package is suitable for high density surface mounting and high speed assembly.

■ Absolute Maximum Ratings $T_a = 25^{\circ}\text{C}$

Parameter	Symbol	Value	Unit
Reverse voltage	V_R	10	V
Average rectified current	I_o	15	mA
Junction temperature	T_j	125	$^{\circ}\text{C}$
Storage temperature	T_{stg}	-55 to +125	$^{\circ}\text{C}$

■ Electrical Characteristics $T_a = 25^{\circ}\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Forward voltage	V_F	$I_F = 1\text{ mA}$	0.35		0.42	V
		$I_F = 10\text{ mA}$	0.50		0.58	
Reverse current	I_R	$V_R = 2\text{ V}$			0.2	$\mu\text{ A}$
		$V_R = 10\text{ V}$			10	
Capacitance	C	$V_R = 0\text{ V}, f = 1\text{ MHz}$			0.80	pF
Capacitance deviation	ΔC	$V_R = 0\text{ V}, f = 1\text{ MHz}$			0.10	pF
Forward voltage deviation	ΔV_F	$I_F = 10\text{ mA}$			10	mV
ESD-Capability (Note 1)		$C=200\text{ pF}, R=0\ \Omega$ Both forward and reverse direction 1 pulse.	30			V

Note

1. Failure criterion ; $I_R \geq 0.4\ \mu\text{ A}$ at $V_R = 2\text{ V}$

■ Marking

Marking	C7
---------	----